

IN THE CLAIMS

Claims 1-16 (Canceled).

17 (Currently Amended). A transistor comprising:
a source region;
a drain region;
a plurality of nanotubes extending between said source and drain regions, said nanotubes having functionalized ends with attached functional groups; and
a gate electrode over said nanotubes.

18 (Original). The transistor of claim 17 wherein said nanotubes are parallel to one another.

19 (Previously Presented). The transistor of claim 17 wherein said nanotubes are spaced equidistantly from one another.

Claim 20 (Canceled).

21 (Previously Presented). The transistor of claim 17 wherein said nanotubes have opposed first functionalized ends coupled to said source region and second functionalized ends coupled to said drain region, said first functionalized ends attracted to said source region and not said drain region.

22 (Original). The transistor of claim 17 wherein said nanotubes are capless.

23 (Previously Presented). A transistor comprising:
a source region;
a drain region;
a plurality of open ended nanotubes extending between said source and drain regions; and
a gate electrode over said nanotubes.

24 (Previously Presented). The transistor of claim 23 wherein said nanotubes are parallel to one another.

25 (Previously Presented). The transistor of claim 23 wherein said nanotubes are spaced equidistantly from one another.

26 (Previously Presented). The transistor of claim 23 wherein said nanotubes have functionalized ends.

27 (Previously Presented). The transistor of claim 23 wherein said nanotubes have opposed first functionalized ends coupled to said source region and second functionalized ends coupled to said drain region, said first functionalized ends attracted to said source region and not said drain region.

28 (New). A transistor comprising:
a source region;
a drain region;
a plurality of nanotubes extending between source and drain regions, each nanotubes including two opposed ends, the opposed ends of each nanotube having different functional groups attached to the opposed ends.

29 (New). The transistor of claim 28 wherein said nanotubes are parallel.

30 (New). The transistor of claim 28 wherein said nanotubes are spaced equidistantly from one another.

31 (New). The transistor of claim 28 wherein said nanotubes have opposed first functionalized ends coupled to said source region and second functionalized ends coupled to said drain regions, said first functionalized ends attracting to said source region and not said drain region.